



of 10000 |

NXH008P120M3F1PTG, NXH008P120M3F1PG

NXH008P120M3F1PTG, NXH008P120M3F1PG

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
SiC MOSFET			
Drain Source Voltage	V_{DSS}	1200	V
Gate Source Voltage	V_{GS}	+22/ 10	V
Continuous Drain Current @ $T_C = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$)	I_D	145	A
Pulsed Drain Current ($T_J = 150^\circ\text{C}$)	I_{Dpulse}	436	A
Maximum Power Dissipation ($T_J = 175^\circ\text{C}$)	P_{tot}	382	W
Minimum Operating Junction Temperature	T_{JMIN}	40	$^\circ\text{C}$
Maximum Operating Junction Temperature	T_{JMAX}	175	$^\circ\text{C}$

THERMAL PROPERTIES

Storage Temperature Range	T_{stg}	40 to 150	$^\circ\text{C}$
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INSULATION PROPERTIES

Isolation Test Voltage, $t = 1$ s, 60 Hz	V_{is}	4800	V_{RMS}
Creepage Distance		12.7	mm
CTI		600	
Substrate Ceramic Material		Al_2O_3	
Substrate Ceramic Material Thickness		0.32	mm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

RECOMMENDED OPERATING RANGES

Rating	Symbol	Min	Max	Unit
Module Operating Junction Temperature	T_J	40	150	$^\circ\text{C}$

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
SiC MOSFET CHARACTERISTICS						
Zero Gate Voltage Drain Current	$V_{GS} = 0$ V, $V_{DS} = 1200$ V, $T_J = 25^\circ\text{C}$	I_{DSS}	–		400	μA
Drain Source On Resistance	$V_{GS} = 18$ V, $I_D = 120$ A, $T_J = 25^\circ\text{C}$	$R_{DS(ON)}$	–	7.7	10.9	m Ω
	$V_{GS} = 18$ V, $I_D = 120$ A, $T_J = 125^\circ\text{C}$			12.6		
	$V_{GS} = 18$ V, $I_D = 120$ A, $T_J = 150^\circ\text{C}$		–	14.4	–	
	$V_{GS} = 18$ V, $I_D = 120$ A, $T_J = 175^\circ\text{C}$			18.1		
Gate Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 60$ mA	$V_{GS(TH)}$	2.04	2.4	4.4	V
Internal Gate Resistance		R_{GINT}		0.8		Ω
Gate Leakage Current	$V_{GS} = 10$ V / 22 V, $V_{DS} = 0$ V	I_{GSS}	–4			

NXH008P120M3F1PTG, NXH008P120M3F1PG

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
SiC MOSFET CHARACTERISTICS						
Turn on Delay Time	$T_J = 25^\circ\text{C}$ $V_{DS} = 800\text{ V}, I_D = 120\text{ A}$ $V_{GS} = 3\text{ V} / 18\text{ V}, R_G = 2\ \Omega$	$t_{d(\text{on})}$	–	17	–	ns
Rise Time		t_r	–	17	–	
Turn off Delay Time		$t_{d(\text{off})}$	–	97	–	
Fall Time		t_f	–	12	–	
Turn on Switching Loss per Pulse		E_{ON}	–	1760	–	μJ
Turn off Switching Loss per Pulse		E_{OFF}	–	588	–	
Turn on Delay Time	$T_J = 150^\circ\text{C}$ $V_{DS} = 800\text{ V}, I_D = 120\text{ A}$ $V_{GS} = 3\text{ V} / 18\text{ V}, R_G = 2\ \Omega$	$t_{d(\text{on})}$	–	15	–	ns
Rise Time		t_r	–	15	–	
Turn off Delay Time		$t_{d(\text{off})}$	–	110	–	
Fall Time		t_f	–	13	–	
Turn on Switching Loss per Pulse		E_{ON}	–	2155	–	μJ
Turn off Switching Loss per Pulse		E_{OFF}	–	745	–	
Diode Forward Voltage	$V_{GS} = 3\text{ V}, I_{SD} = 120\text{ A}, T_J = 25^\circ\text{C}$	V_{SD}	–	4.67	6.2	V
	$V_{GS} = 3\text{ V}, I_{SD} = 120\text{ A}, T_J = 125^\circ\text{C}$		–	4.45	–	
	$V_{GS} = 3\text{ V}, I_{SD} = 120\text{ A}, T_J = 150^\circ\text{C}$					

NXH008P120M3F1PTG, NXH008P120M3F1PG

TYPICAL CHARACTERISTICS M1/M2 SIC MOSFET CHARACTERISTIC

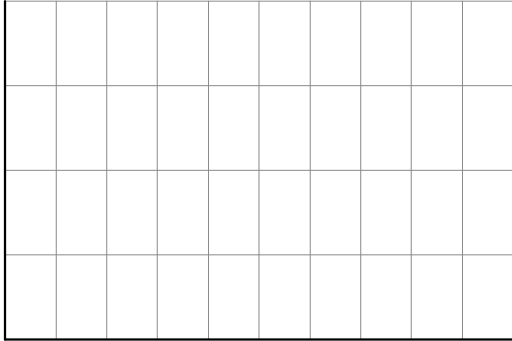


Figure 8. Switching on Loss vs. Drain
Current $V_{DS} = 600\text{ V}$

Figure 9. Switching on Loss vs. Gate
Resistance $V_{DS} = 600\text{ V}$

Figure 10. Switching off Loss vs. Drain
Current $V_{DS} = 600\text{ V}$

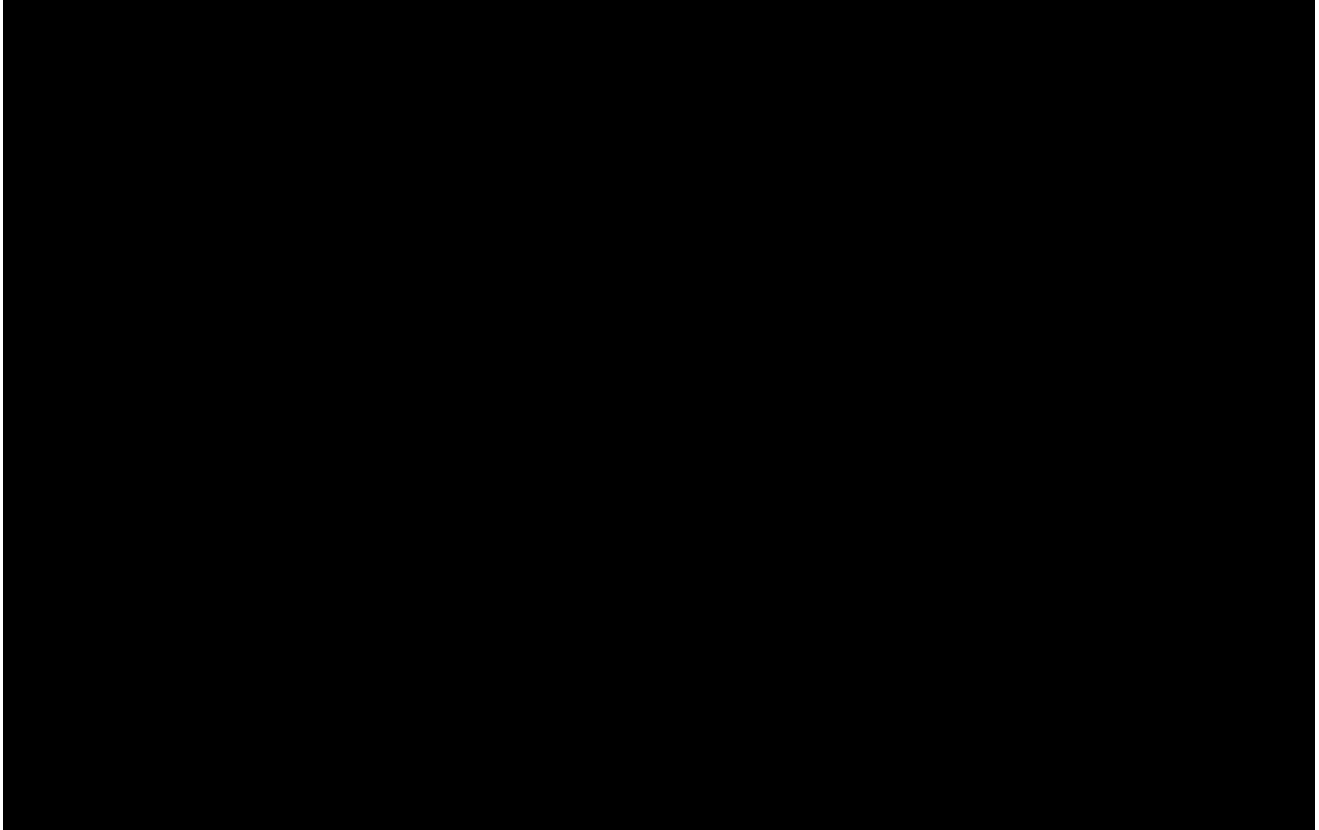
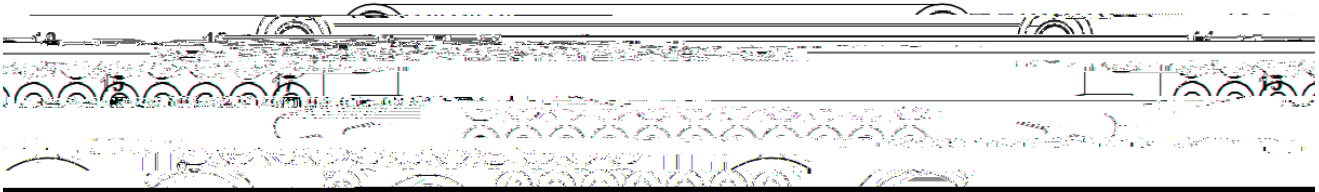
Figure 11. Switching off Loss vs. Gate
Resistance $V_{DS} = 600\text{ V}$

Figure 12. Switching on Loss vs. Drain
Current $V_{DS} = 800\text{ V}$

Figure 13. Switching on Loss vs. Gate
Resistance $V_{DS} = 800\text{ V}$

PIN POSITION INFORMATION

scale = 2.5 : 1



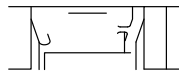
PIM18 33.8x42.5 (PRESS FIT)
CASE 180BW
ISSUE B

DATE 30 APR 2021

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17.00

53.10
63.5

2.40



**GENERIC
MARKING DIAGRAM***



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